

# PUMD15/ZLF Datasheet



DiGi Electronics Part Number PUMD15/ZLF-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PUMD15/ZLF

Description TRANS PREBIAS

Detailed Description Pre-Biased Bipolar Transistor (BJT) 1 NPN, 1 PNP - P

re-Biased (Dual) 50V 100mA 230MHz, 180MHz 300m

W Surface Mount 6-TSSOP

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PUMD15/ZLF	Nexperia USA Inc.
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
1 NPN, 1 PNP - Pre-Biased (Dual)	100mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50V	4.7kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
4.7kOhms	30 @ 10mA, 5V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
150mV @ 500μA, 10mA	1μΑ
Frequency - Transition:	Power - Max:
230MHz, 180MHz	300mW
Grade:	Qualification:
Automotive	AEC-Q101
Mounting Type:	Package / Case:
Surface Mount	6-TSSOP, SC-88, SOT-363
Supplier Device Package:	Base Product Number:
6-TSSOP	PUMD15

# **Environmental & Export classification**

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RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	OBSOLETE
HTSUS:	



# **PUMD15**

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

31 March 2023

Product data sheet

# 1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH15 PNP/PNP complement: PUMB15

## 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplified circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

## 3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replacement of general purpose transistors in digital applications

## 4. Quick reference data

Table 1. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	-	50	V
I <sub>O</sub>	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	

- [1] For the PNP transistor (TR2) with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2 006aaa143

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package				
	Name	Description	Version		
PUMD15		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>		

## 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD15	D0%

[1] % = placeholder for manufacturing site code

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or					
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	[1]	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	[1]	-	10	V
V <sub>I</sub>	input voltage	TR1 (NPN)		-10	30	V
		TR2 (PNP)		-30	10	V
Io	output current		[1]	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	200	mW
Per device				'		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] For the PNP transistor (TR2) with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

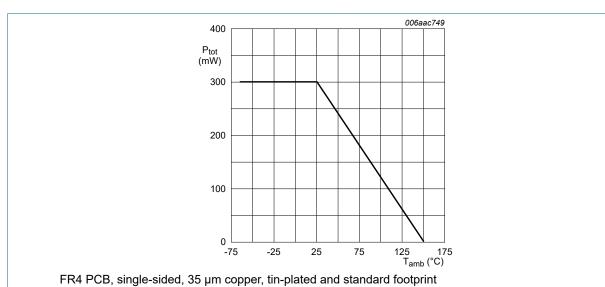


Fig. 1. Per device: Power derating curve

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

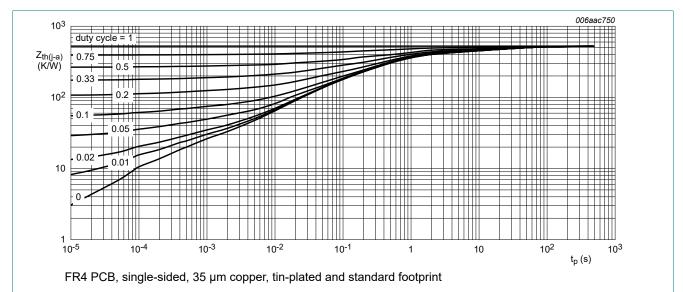


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 10. Characteristics

#### **Table 7. Characteristics**

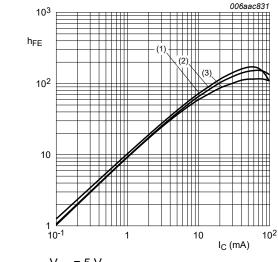
Parameter	Conditions		Min	Тур	Max	Unit
or						<b> </b>
collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	[1]	-	-	5	μΑ
emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	900	μA
DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C	[1]	30	-	-	
collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	[1]	-	1.1	0.5	V
on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C	[1]	2.5	1.9	-	V
bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ
bias resistor ratio		[2]	0.8	1	1.2	
						•
collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[3]	-	230	-	MHz
collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF
transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[3]	-	180	-	MHz
	collector-base breakdown voltage  collector-emitter breakdown voltage  collector-base cut-off current  collector-emitter cut-off current  emitter-base cut-off current  DC current gain  collector-emitter saturation voltage  off-state input voltage  on-state input voltage bias resistor 1 (input)  bias resistor ratio  collector capacitance  transition frequency	collector-base breakdown voltage	collector-base breakdown voltage	collector-base breakdown voltage $I_C = 100  \mu A$ ; $I_E = 0  A$ ; $T_{amb} = 25  ^{\circ} C$ [1]         50           collector-emitter breakdown voltage $I_C = 2  \text{mA}$ ; $I_B = 0  \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         50           collector-emitter breakdown voltage $V_{CB} = 50  \text{V}$ ; $I_E = 0  \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           collector-base cut-off current $V_{CE} = 30  \text{V}$ ; $I_B = 0  \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           collector-emitter cut-off current $V_{CE} = 30  \text{V}$ ; $I_B = 0  \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           emitter-base cut-off current $V_{CE} = 5  \text{V}$ ; $I_C = 0  \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           collector-emitter saturation voltage $V_{CE} = 5  \text{V}$ ; $I_C = 10  \text{mA}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           collector-emitter saturation voltage $V_{CE} = 5  \text{V}$ ; $I_C = 100  \mu \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           on-state input voltage $V_{CE} = 5  \text{V}$ ; $I_C = 100  \mu \text{A}$ ; $T_{amb} = 25  ^{\circ} \text{C}$ [1]         -           bias resistor 1 (input)         [2]         3.3           bias resistor ratio         [2]         0.8    collector capacitance $V_{CB} = 10  \text{V}$ ; $I_C = 10  \text{mA}$ ; $I_C = 0  \text{A}$ ; $I_C = 0  \text{A}$ ;	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$

<sup>[1]</sup> For the PNP transistor (TR2) with negative polarity.

<sup>[2]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[3]</sup> Characteristics of built-in transistor

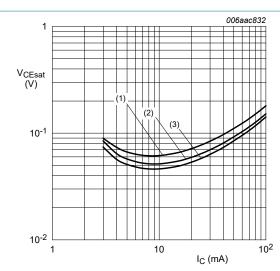
#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$



 $V_{CE} = 5 V$ (1)  $T_{amb} = 100 °C$ 

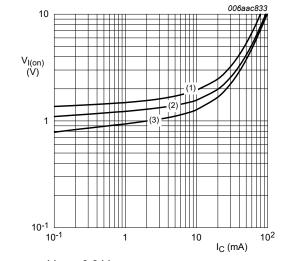
(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



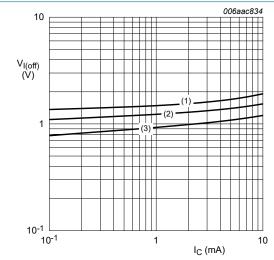
 $V_{CE}$  = 0.3 V

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$ 

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 kΩ, R2 = 4.7 kΩ

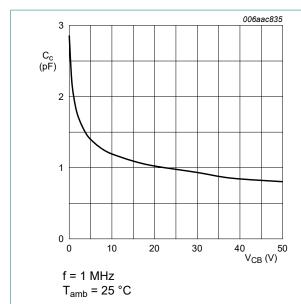
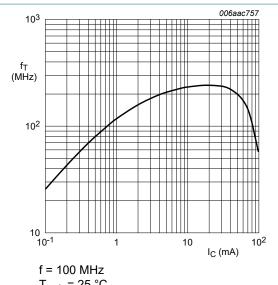
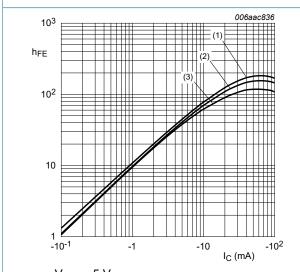


Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



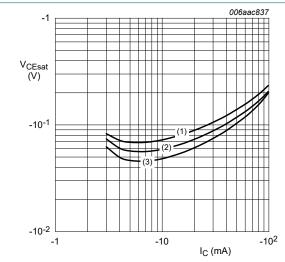
f = 100 MHz  $T_{amb} = 25 \text{ °C}$  $V_{CE} = 5 \text{ V}$ 

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values

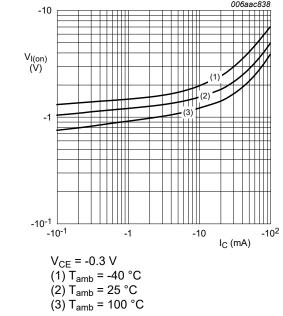


 $I_{\rm C}/I_{\rm B} = 20$ (1)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = -40~{\rm ^{\circ}C}$ 

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

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#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$





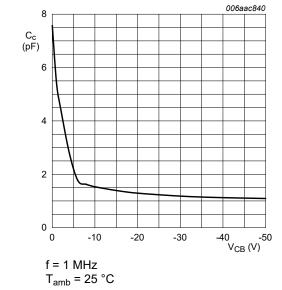
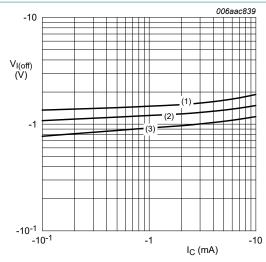


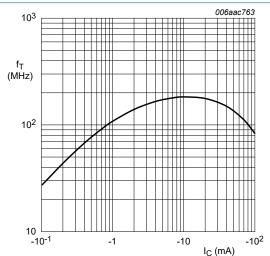
Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



V<sub>CE</sub> = -5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

of collector current; typical values



f = 100 MHz

 $T_{amb}$  = 25 °C

 $V_{CE} = -5 V$ 

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

## 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

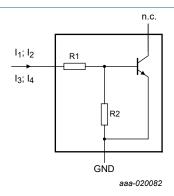


Fig. 15. NPN transistor: Resistor test circuit

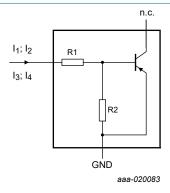


Fig. 16. PNP transistor: Resistor test circuit

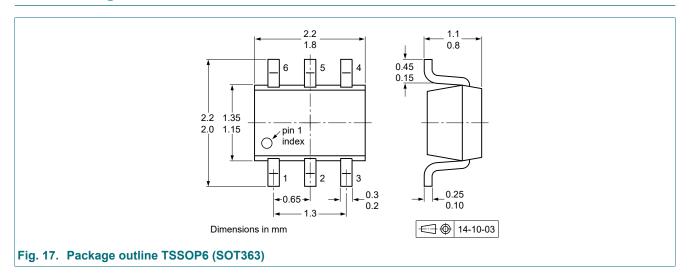
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

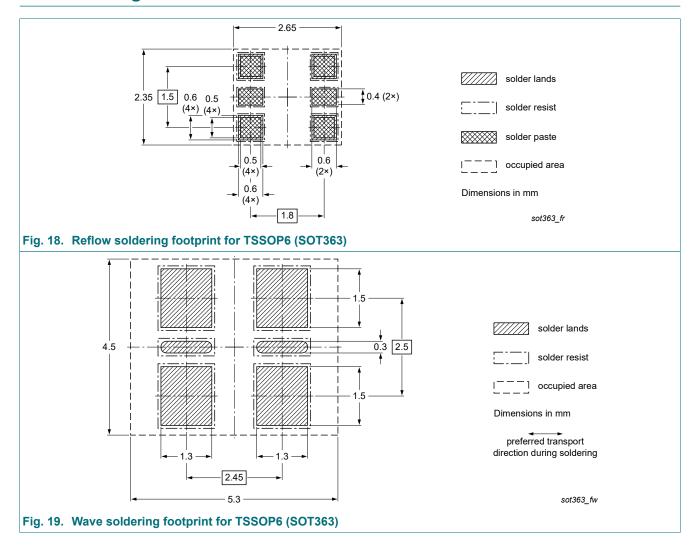
PUMD15	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14
TR1 (NPN)	4.7	4.7	600 μΑ	700 μΑ	-600 μΑ	-700 μA
TR2 (PNP)	4.7	4.7	-600 μΑ	-700 μA	600 μΑ	700 µA

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 12. Package outline



# 13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PUMD15 v.5	20230331	Product data sheet	-	PEMD15_PUMD15 v.4	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Family data sheet reduced to single type data sheet.</li> <li>Packing information removed.</li> </ul>				
PEMD15_PUMD15 v.4	20111219	Product data sheet	-	PEMD15_PUMD15 v.3	
PEMD15_PUMD15 v.3	20090902	Product data sheet	-	PEMD15_PUMD15 v.2	
PEMD15_PUMD15 v.2	20050425	Product data sheet	-	PUMD15 v.1	
PUMD15 v.1	20040204	Product specification	-	-	

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

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PUMD15

## 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

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